Shinji Migita

List of Publications by Year
in descending order

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164	2,232	361413	302126
papers	citations	20 h-index	39 g-index

164	164	164	2146
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Enhancement of ferroelectricity in sputtered HZO thin films by catalytically generated atomic hydrogen treatment. Japanese Journal of Applied Physics, 2022, 61, SH1004.	1.5	2
2	Impact of annealing on electric and elastic properties of 10-nm Hf0.5Zr0.5O2 films prepared on Si by sputtering. Microelectronic Engineering, 2022, 258, 111770.	2.4	1
3	Lateral variations of the surface electric potential and elastic stiffness of ultrathin Hf0.5Zr0.5O2 films on silicon. AIP Advances, 2021, 11, 015216.	1.3	4
4	Thermal stability of ferroelectricity in hafniumâ€“zirconium dioxide films deposited by sputtering and chemical solution deposition for oxide-channel ferroelectric-gate transistor applications. Applied Physics Express, 2021, 14, 041006.	2.4	6
5	Accelerated ferroelectric phase transformation in HfO₂/ZrO₂ nanolaminates. Applied Physics Express, 2021, 14, 051006.	2.4	15
6	Impact of reduced pressure crystallization on ferroelectric properties in hafnium-zirconium dioxide films deposited by sputtering. Japanese Journal of Applied Physics, 2021, 60, SFFB05.	1.5	8
7	Investigation of the wake-up process and time-dependent imprint of Hf0.5Zr0.5O2 film through the direct piezoelectric response. Applied Physics Letters, 2021, 119, .	3.3	6
8	Regulating phase transformation kinetics via redox reaction in ferroelectric Ge-doped HfO2. Applied Physics Letters, 2020, 117, .	3.3	9
9	Device simulation of negative-capacitance field-effect transistors with a uniaxial ferroelectric gate insulator. Nonlinear Theory and Its Applications IEICE, 2020, 11, 145-156.	0.6	1
10	Robustness of Ferroelectricity in Hafnium-Zirconium Dioxide Films Deposited By Sputtering and Chemical Solution Deposition for Ferroelectric Transistor Applications. ECS Meeting Abstracts, 2020, MA2020-02, 1371-1371.	0.0	0
11	Design points of ferroelectric field-effect transistors for memory and logic applications as investigated by metal-ferroelectric-metalâ€“insulatorâ€“semiconductor gate stack structures using Hf_{0.5}Zr_{0.5}O₂ films. Japanese Journal of Applied Physics, 2019, 58, SLLB06.	1.5	6
12	Ferroelectric Films by Physical Vapor Deposition and Ion Implantation. , 2019, , 103-125.		0
13	Phase transformation behavior of ultrathin Hf_{0.5}Zr_{0.5}O₂ films investigated through wide range annealing experiments. Japanese Journal of Applied Physics, 2019, 58, SBBA07.	1.5	38
14	Evolution of ferroelectric HfO2 in ultrathin region down to 3â€‰nm. Applied Physics Letters, 2018, 112, .	3.3	188
15	Polarization switching behavior of Hfâ€“Zrâ€“O ferroelectric ultrathin films studied through coercive field characteristics. Japanese Journal of Applied Physics, 2018, 57, 04FB01.	1.5	79
16	Simulation study of short-channel effects of tunnel field-effect transistors. Japanese Journal of Applied Physics, 2018, 57, 04FD04.	1.5	3
17	Design of steep-slope negative-capacitance FinFETs for dense integration: Importance of appropriate ferroelectric capacitance and short-channel effects. Japanese Journal of Applied Physics, 2018, 57, 04FD03.	1.5	2
18	Fringing field effects in negative capacitance field-effect transistors with a ferroelectric gate insulator. Japanese Journal of Applied Physics, 2018, 57, 04FD07.	1.5	16

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19	Assessment of Steep-Subthreshold Swing Behaviors in Ferroelectric-Gate Field-Effect Transistors Caused by Positive Feedback of Polarization Reversal. , 2018, , .		2
20	Multidomain Dynamics of Ferroelectric Polarization and its Coherency-Breaking in Negative Capacitance Field-Effect Transistors. , 2018, , .		9
21	One-dimensional array of gold nanoparticles fabricated using biotemplate and its application to fine FET. Japanese Journal of Applied Physics, 2018, 57, 06HC05.	1.5	2
22	Thermodynamic control of ferroelectric-phase formation in HfxZr1â^'xO2 and ZrO2. Journal of Applied Physics, 2018, 124, .	2.5	48
23	Device Simulation of Negative-Capacitance Field-Effect Transistors With a Ferroelectric Gate Insulator. , 2018, , .		3
24	Ultrashort intrinsic-like channel FETs with nanodot-type floating gate utilizing biomaterial. Japanese Journal of Applied Physics, 2018, 57, 125003.	1.5	0
25	Structural and electrical characterization of epitaxial Ge thin films on Si(001) formed by sputtering. Japanese Journal of Applied Physics, 2017, 56, 04CB01.	1.5	0
26	On the drain bias dependence of long-channel silicon-on-insulator-based tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CD04.	1.5	2
27	Tunnel FinFET CMOS inverter with very low short-circuit current for ultralow-power Internet of Things application. Japanese Journal of Applied Physics, 2017, 56, 04CD19.	1.5	15
28	Impact of residual defects caused by extension ion implantation in FinFETs on parasitic resistance and its fluctuation. Solid-State Electronics, 2017, 132, 103-108.	1.4	3
29	Bias temperature instability in tunnel field-effect transistors. Japanese Journal of Applied Physics, 2017, 56, 04CA04.	1.5	2
30	Kinetic pathway of the ferroelectric phase formation in doped HfO2 films. Journal of Applied Physics, 2017, 122, .	2.5	150
31	Thickness-independent behavior of coercive field in HfO<inf>2</inf>-based ferroelectrics. , 2017, , .		6
32	Epitaxial growth of Ge thin film on Si (001) by DC magnetron sputtering. Materials Science in Semiconductor Processing, 2017, 70, 3-7.	4.0	4
33	Suppression of tunneling rate fluctuations in tunnel field-effect transistors by enhancing tunneling probability. Japanese Journal of Applied Physics, 2017, 56, 04CD02.	1.5	5
34	(Invited) Relationship between Ferroelectricity and Electrical Breakdown in Hf-Zr-O Thin Films. ECS Transactions, 2017, 80, 247-252.	0.5	6
35	Estimation of charge effects of ultrafine channel utilizing junctionless transistor with nanodot-type floating gate. Japanese Journal of Applied Physics, 2017, 56, 03BB05.	1.5	0
36	Perspective of negative capacitance FinFETs investigated by transient TCAD simulation. , 2017, , .		17

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37	Structural advantages of silicon-on-insulator FETs over FinFETs in steep subthreshold-swing operation in ferroelectric-gate FETs. Japanese Journal of Applied Physics, 2017, 56, 04CD10.	1.5	9
38	One-dimensional arrangement of nanoparticles utilizing the V-groove and cage shaped proteins. Japanese Journal of Applied Physics, 2017, 56, 06GG11.	1.5	0
39	Design and simulation of steep-slope silicon-on-insulator FETs using negative capacitance: Impact of buried oxide thickness and remnant polarization. , 2016, , .		1
40	Ferroelectric phase stabilization of HfO₂ by nitrogen doping. Applied Physics Express, 2016, 9, 091501.	2.4	84
41	Fully coupled 3-D device simulation of negative capacitance FinFETs for sub 10 nm integration. , 2016, , .		77
42	Demonstrating performance improvement of complementary TFET circuits by I<inf>on</inf> enhancement based on isoelectronic trap technology. , 2016, , .		9
43	General relationship for cation and anion doping effects on ferroelectric HfO<inf>2</inf> formation. , 2016, , .		14
44	Material and device engineering in fully depleted silicon-on-insulator transistors to realize a steep subthreshold swing using negative capacitance. Japanese Journal of Applied Physics, 2016, 55, 08PD01.	1.5	20
45	Charge effects of ultrafine FET with nanodot type floating gate. , 2016, , .		1
46	Ferroelectricity of nondoped thin HfO₂ films in TiN/HfO₂/TiN stacks. Japanese Journal of Applied Physics, 2016, 55, 08PB01.	1.5	68
47	Steep subthreshold swing and energy efficiency in MOSFFETs utilizing nonlinear gate dielectric insulators. Japanese Journal of Applied Physics, 2016, 55, 04ED02.	1.5	2
48	Study of wake-up and fatigue properties in doped and undoped ferroelectric HfO<inf>2</inf> in conjunction with piezo-response force microscopy analysis. , 2016, , .		6
49	Impact of extension implantation conditions of fin field-effect transistors on gate-induced drain leakage. Japanese Journal of Applied Physics, 2016, 55, 04EB01.	1.5	3
50	(Invited) Floating Gate Type SOI-FinFET Flash Memories with Different Channel Shapes and Interpoly Dielectric Materials. ECS Transactions, 2016, 72, 11-24.	0.5	1
51	Introduction of SiGe/Si heterojunction into novel multilayer tunnel FinFET. Japanese Journal of Applied Physics, 2016, 55, 04EB06.	1.5	15
52	Robust and compact key generator using physically unclonable function based on logic-transistor-compatible poly-crystalline-Si channel FinFET technology. , 2015, , .		5
53	Heated ion implantation for high-performance and highly reliable silicon-on-insulator complementary metalâ€“oxideâ€“silicon fin field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 04DA06.	1.5	4
54	Understanding of BTI for tunnel FETs. , 2015, , .		2

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55	Impact of granular work function variation in a gate electrode on low-frequency noise for fin field-effect transistors. Applied Physics Express, 2015, 8, 044201.	2.4	7
56	Modeling of parallel electric field tunnel FETs. , 2015, , .		0
57	Effect of hot implantation on ON-current enhancement utilizing isoelectronic trap in Si-based tunnel field-effect transistors. Applied Physics Express, 2015, 8, 036503.	2.4	9
58	Ultra-short channel junctionless transistor with a one-dimensional nanodot array floating gate. Applied Physics Letters, 2015, 106, .	3.3	7
59	Impact of fin length on threshold voltage modulation by back bias for Independent double-gate tunnel fin field-effect transistors. Solid-State Electronics, 2015, 111, 62-66.	1.4	3
60	Highly Vt tunable and low variability triangular fin-channel MOSFETs on SOTB. Microelectronic Engineering, 2015, 147, 290-293.	2.4	0
61	Study of gate leakage current paths in p-channel tunnel field-effect transistor by current separation measurement and device simulation. Japanese Journal of Applied Physics, 2015, 54, 034202.	1.5	1
62	Improvement of epitaxial channel quality on heavily arsenic- and boron-doped Si surfaces and impact on performance of tunnel field-effect transistors. Solid-State Electronics, 2015, 113, 173-178.	1.4	6
63	Study of tunneling transport in Si-based tunnel field-effect transistors with ON current enhancement utilizing isoelectronic trap. Applied Physics Letters, 2015, 106, .	3.3	54
64	PBTI for N-type tunnel FinFETs. , 2015, , .		1
65	Evolution of nanoscale silicon CMOS technology for ultra low power application. , 2015, , .		0
66	Channel shape and interpoly dielectric material effects on electrical characteristics of floating-gate-type three-dimensional fin channel flash memories. Japanese Journal of Applied Physics, 2015, 54, 04DD04.	1.5	2
67	Comparative Study of Charge Trapping Type SOI-FinFET Flash Memories with Different Blocking Layer Materials. Journal of Low Power Electronics and Applications, 2014, 4, 153-167.	2.0	5
68	Unexpected equivalent-oxide-thickness dependence of the subthreshold swing in tunnel field-effect transistors. Applied Physics Express, 2014, 7, 024201.	2.4	35
69	Scaling breakthrough for analog/digital circuits by suppressing variability and low-frequency noise for FinFETs by amorphous metal gate technology. , 2014, , .		4
70	Variation behavior of tunnel-FETs originated from dopant concentration at source region and channel edge configuration. , 2014, , .		4
71	TDDB characteristics of thin polycrystalline and amorphous HfO<inf>2</inf> films. , 2014, , .		2
72	Experimental realization of complementary p- and n- tunnel FinFETs with subthreshold slopes of less than 60 mV/decade and very low (pA/μm) off-current on a Si CMOS platform. , 2014, , .		18

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73	Band-to-band tunneling current enhancement utilizing isoelectronic trap and its application to TFETs. , 2014, , .		22
74	Accurate prediction of PBTI lifetime for N-type fin-channel tunnel FETs. , 2014, , .		10
75	Importance of interface engineering for synthesis of SrHfO₃ perovskite thin films on Si substrates through crystallization of amorphous films and control of flat-band voltages of metalâ€“oxideâ€“semiconductor capacitors. Japanese Journal of Applied Physics, 2014, 53, 04EA03.	1.5	4
76	Influence of work function variation of metal gates on fluctuation of sub-threshold drain current for fin field-effect transistors with undoped channels. Japanese Journal of Applied Physics, 2014, 53, 04EC11.	1.5	12
77	Experimental study of three-dimensional fin-channel charge trapping flash memories with titanium nitride and polycrystalline silicon gates. Japanese Journal of Applied Physics, 2014, 53, 04ED16.	1.5	2
78	(Invited) Charge Trapping Type SOI-FinFET Flash Memory. ECS Transactions, 2014, 61, 263-280.	0.5	4
79	Performance Enhancement of Tunnel Field-Effect Transistors by Synthetic Electric Field Effect. IEEE Electron Device Letters, 2014, 35, 792-794.	3.9	53
80	Predictivity of the non-local BTBT model for structure dependencies of tunnel FETs. , 2014, , .		9
81	Fluctuation in drain induced barrier lowering (DIBL) for FinFETs caused by granular work function variation of metal gates. , 2014, , .		2
82	Performance evaluation of parallel electric field tunnel field-effect transistor by a distributed-element circuit model. Solid-State Electronics, 2014, 102, 82-86.	1.4	7
83	Lowest variability SOI FinFETs having multiple V<inf>t</inf> by back-biasing. , 2014, , .		9
84	Experimental Demonstration of Ultrashort-Channel (3 nm) Junctionless FETs Utilizing Atomically Sharp V-Grooves on SOI. IEEE Nanotechnology Magazine, 2014, 13, 208-215.	2.0	59
85	Fabrication and characterization of 3D fin-channel MANOS type flash memory. , 2014, , .		1
86	Experimental study of charge trapping type FinFET flash memory. , 2014, , .		0
87	Impact of atomic-scale structural design on ultra-short channel (3 nm) MOSFETs. , 2013, , .		1
88	Variability of short channel junctionless field-effect transistors caused by fluctuation of dopant concentration. , 2013, , .		1
89	Analysis of threshold voltage shifts in double gate tunnel FinFETs: Effects of improved electrostatics by gate dielectrics and back gate effects. , 2013, , .		3
90	Performance limit of parallel electric field tunnel FET and improvement by modified gate and channel configurations. , 2013, , .		4

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91	Two-step annealing effects on ultrathin EOT higher-k (k=40) ALD-HfO2 gate stacks. Solid-State Electronics, 2013, 84, 58-64.	1.4	11
92	Analysis of Vth flexibility in ultrathin-BOX SOI FinFETs. , 2013, , .		0
93	A compact model for tunnel field-effect transistors incorporating nonlocal band-to-band tunneling. Journal of Applied Physics, 2013, 114, 144512.	2.5	25
94	Tunnel Field-Effect Transistor with Epitaxially Grown Tunnel Junction Fabricated by Source/Drain-First and Tunnel-Junction-Last Processes. Japanese Journal of Applied Physics, 2013, 52, 04CC25.	1.5	16
95	(Invited) Extremely Short Channel Si-MOSFETs Prepared on SOI Substrates Using Anisotropic Wet Etching. ECS Transactions, 2013, 58, 273-280.	0.5	0
96	Guidelines for symmetric threshold voltage in tunnel FinFETs with single and dual metal gate electrodes. , 2013, , .		1
97	Suppression of threshold voltage variability of double-gate fin field-effect transistors using amorphous metal gate with uniform work function. Applied Physics Letters, 2013, 102, .	3.3	15
98	Fabrication and Demonstration of 3-nm-Channel-Length Junctionless Field-Effect Transistors on Silicon-on-Insulator Substrates Using Anisotropic Wet Etching and Lateral Diffusion of Dopants. Japanese Journal of Applied Physics, 2013, 52, 04CA01.	1.5	21
99	Heated ion implantation technology for highly reliable metal-gate/high-k CMOS SOI FinFETs. , 2013, , .		5
100	Suppressed variability of current-onset voltage of FinFETs by improvement of work function uniformity of metal gates. , 2013, , .		0
101	Extremely Scaled (${sim}0.2$ nm) Equivalent Oxide Thickness of Higher-k ($k = 40$) HfO$_{2}$ Gate Stacks Prepared by Atomic Layer Deposition and Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2012, 51, 02BA04.	1.5	4
102	Enhancement of the ultraviolet absorption and Raman efficiencies of a few nanometer thick Si-on-insulator. Journal of Applied Physics, 2012, 112, 074317.	2.5	10
103	Two-step annealing effects on ultrathin EOT higher-k (k = 40) ALD-HfO<inf>2</inf> gate stacks. , 2012, , .		0
104	Experimental Comparisons between Tetrakis(dimethylamino)titanium Precursor-Based Atomic-Layer-Deposited and Physical-Vapor-Deposited Titaniumâ€“Nitride Gate for High-Performance Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA05.	1.5	0
105	Extremely Scaled Equivalent Oxide Thickness of High-k (k=40) HfO2 Gate Stacks Prepared by Atomic Layer Deposition and Ti Cap Anneal. Hyomen Kagaku, 2012, 33, 610-615.	0.0	0
106	First demonstration of drain current enhancement in SOI tunnel FET with vertical-tunnel-multiplication. , 2012, , .		6
107	Suppressing V<inf>t</inf> and G<inf>m</inf> variability of FinFETs using amorphous metal gates for 14 nm and beyond. , 2012, , .		22
108	Cryogenic operation of double-gate FinFET and demonstration of analog circuit at 4.2K. , 2012, , .		2

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109	Electrical performances of junctionless-FETs at the scaling limit (L<inf>CH</inf>) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 5		25
110	Exact control of junction position using epitaxial NiSi2 crystallization in ultrathin silicon-on-insulator metal-oxide-semiconductor field-effect transistors. AIP Advances, 2012, 2, .	1.3	1
111	Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653.	3.0	14
112	Decomposition of On-Current Variability of nMOS FinFETs for Prediction Beyond 20 nm. IEEE Transactions on Electron Devices, 2012, 59, 2003-2010.	3.0	27
113	Extremely Scaled (â^¼0.2 nm) Equivalent Oxide Thickness of Higher-k(k= 40) HfO2Gate Stacks Prepared by Atomic Layer Deposition and Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2012, 51, 02BA04.	1.5	7
114	Influence of fin height on poly-Si/PVD-TiN stacked gate FinFET performance. , 2011, , .		0
115	(Invited) Epitaxial HfO₂ Thin Films on Si Substrates: Strategy for Sub-1 nm EOT Technology. ECS Transactions, 2011, 41, 135-144.	0.5	3
116	Nature of interface traps in Ge metal-insulator-semiconductor structures with GeO2 interfacial layers. Journal of Applied Physics, 2011, 109, .	2.5	18
117	Accurate evaluation of Ge metalâ€"insulatorâ€"semiconductor interface properties. Journal of Applied Physics, 2011, 110, .	2.5	14
118	Fabrication of Direct-Contact Higher-k HfO₂ Gate Stacks by Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PG01.	1.5	14
119	Fabrication of Direct-Contact Higher-kHfO₂Gate Stacks by Oxygen-Controlled Cap Post-Deposition Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PG01.	1.5	5
120	Fabrication of High-k Gate Insulator Films by Atomic Layer Deposition and Their Properties Influenced by Substrate Hydrophilicity. Journal of the Vacuum Society of Japan, 2011, 54, 105-109.	0.3	0
121	AFM measurement of atomic-scale Si surface etching by active oxidation. Surface Science, 2010, 604, 1432-1437.	1.9	6
122	Effect of Ge Metalâ€“Insulatorâ€“Semiconductor Interfacial Layers on Interface Trap Density near the Conduction Band Edge. Japanese Journal of Applied Physics, 2010, 49, 04DA09.	1.5	3
123	Physical origins of mobility enhancement of Ge p-channel metal-insulator-semiconductor field effect transistors with Si passivation layers. Journal of Applied Physics, 2010, 108, 104511.	2.5	20
124	Impact of Minorty Carrier Response on Characterization of Ge MIS Interface Traps. ECS Transactions, 2009, 19, 117-128.	0.5	0
125	Structural Metastability and Size Scalability of Phase-Controlled HfO2 Formed through Cap-PDA. ECS Transactions, 2009, 19, 563-575.	0.5	7
126	Inversion Layer Mobility in High-k Dielectric MOSFETs - Intrinsic Mobility Degradation by Electric Dipoles at High-k/SiO2 Interface. ECS Transactions, 2009, 16, 67-75.	0.5	0

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127	Growth mechanism of epitaxial NiSi<inf>2</inf> in atomic-scale for Schottky source/drain in Silicon Nanowire transistors. , 2009, , .		2
128	Impact of Surface Hydrophilicization prior to Atomic Layer Deposition for HfO₂/Si Direct-Contact Gate Stacks. Applied Physics Express, 2009, 2, 011201.	2.4	16
129	(111)-Faceted Metal Source and Drain for Aggressively Scaled Metal/High-<formula formulatype="inline"><tex> k</tex></formula> MISFETs. IEEE Transactions on Electron Devices, 2008, 55, 1244-1249.	3.0	18
130	Experimental evidence for the flatband voltage shift of high-k metal-oxide-semiconductor devices due to the dipole formation at the high-kâˆ•SiO2 interface. Applied Physics Letters, 2008, 92, .	3.3	140
131	Design and demonstration of very high-k (k∼50) HfO<inf>2</inf> for ultra-scaled Si CMOS. , 2008, , .		20
132	Achievement of Higher-k and High-Î¦ in Phase Controlled HfO2 Film Using Post Gate Electrode Deposition Annealing. ECS Transactions, 2007, 11, 35-45.	0.5	18
133	Gate-First Processed FUSI/HfO<inf>2</inf>/HfSiO<inf>x</inf>/Si MOSFETs with EOT=0.5 nm - Interfacial Layer Formation by Cycle-by-Cycle Deposition and Annealing. , 2007, , .		8
134	Re-examination of Flat-Band Voltage Shift for High-k MOS Devices. , 2007, , .		22
135	Intrinsic Origin of Electron Mobility Reduction in High-k MOSFETs - From Remote Phonon to Bottom Interface Dipole Scattering. , 2007, , .		22
136	Comprehensive Study of V<inf>FB</inf> Shift in High-k CMOS - Dipole Formation, Fermi-level Pinning and Oxygen Vacancy Effect. , 2007, , .		39
137	Symmetrical threshold voltage in complementary metal-oxide-semiconductor field-effect transistors with HfAlOx(N) achieved by adjusting Hfâˆ•Al compositional ratio. Journal of Applied Physics, 2006, 99, 054506.	2.5	21
138	Silicon-Atom Induced Fermi-Level Pinning of Fully Silicided Platinum Gates on HfO2Dielectrics. Japanese Journal of Applied Physics, 2005, 44, 2267-2272.	1.5	6
139	Study on Oxynitride Buffer Layers in HfO2Metalâ€“Insulatorâ€“Semiconductor Structures for Improving Metalâ€“Insulatorâ€“Semiconductor Field-Effect Transistor Performance. Japanese Journal of Applied Physics, 2005, 44, 1698-1703.	1.5	6
140	Nanometer-scale crystallization of thin HfO2 films studied by HF-chemical etching. Applied Physics Letters, 2005, 86, 212907.	3.3	18
141	Fabrication and electrical properties of ferroelectric-gate FETS with epitaxial gate structures. Electronics and Communications in Japan, 2004, 87, 24-33.	0.2	0
142	Memory properties of a ferroelectric gate field-effect transistor with an adjoining metalâ€“ferroelectricâ€“metal assistance cell. Journal of Applied Physics, 2003, 94, 2559-2562.	2.5	14
143	Fabrication and critical currents of thin-film-type Bi2Sr2CaCu2Ox intrinsic Josephson junctions. Physica C: Superconductivity and Its Applications, 2001, 362, 256-260.	1.2	10
144	Fabrication and Electrical Characteristics of a Trench-Type Metal-Ferroelectric-Metal-Insulator-Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2001, 40, 5605-5609.	1.5	1

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145	Epitaxial structure SrTiO3â€˜011â€‰ on Siâ€˜001â€‰. Journal of Applied Physics, 2001, 89, 5421-5424.	2.5	21
146	All-perovskite-oxide ferroelectric memory transistor composed of Bi2Sr2CuOx and PbZr0.5Ti0.5O3 films. Journal of Applied Physics, 2001, 89, 8153-8158.	2.5	13
147	Epitaxial structure SrBi2Ta2O9‹116› /SrTiO3‹011› /Ce0.12Zr0.88O2‹001› /Si‹001› for ferroelectric-gate FET memory. Integrated Ferroelectrics, 2001, 40, 135-143.	0.7	5
148	Epitaxial Growth of Bi4Ti3O12/CeO2/Ce0.12Zr0.88O2and Bi4Ti3O12/SrTiO3/Ce0.12Zr0.88O2Thin Films on Si and Its Application to Metal-Ferroelectric-Insulator-Semiconductor Diodes. Japanese Journal of Applied Physics, 2000, 39, 5505-5511.	1.5	6
149	Surface Morphology and Dielectric Properties of Stoichiometric and Off-Stoichiometric SrTiO3 Thin Films Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1535-L1537.	1.5	10
150	Growth Style of Bi4Ti3O12Thin Films on CeO2/Ce0.12Zr0.88O2Buffered Si Substrates. Japanese Journal of Applied Physics, 1999, 38, 5411-5416.	1.5	10
151	Magnetic anomaly of Y1â˜’xSrxVO3â˜’Î´. Physica C: Superconductivity and Its Applications, 1999, 317-318, 464-470.	1.2	9
152	Particle-free superconducting Bi2Sr2CaCu2Ox ultrathin films prepared by atomic-layer-controlled molecular beam epitaxy technique. Physica C: Superconductivity and Its Applications, 1999, 311, 42-48.	1.2	14
153	Epitaxial Bi4Ti3O12 thin film growth using Bi self-limiting function. Journal of Crystal Growth, 1999, 200, 161-168.	1.5	24
154	Pulsed laser deposition and ferroelectric properties of SrBi2Ta2O9 thin films. Materials Letters, 1999, 38, 406-412.	2.6	12
155	Molecular beam epitaxial growth of BSCCO and Bi-based oxides: self-limiting growth of the Bi element. , 1998, , .		0
156	Evaluation of Ozone Condensation System by Thermal Decomposition Method. Japanese Journal of Applied Physics, 1997, 36, 94-97.	1.5	1
157	Self-limiting process for the bismuth content in molecular beam epitaxial growth of Bi2Sr2CuOy thin films. Applied Physics Letters, 1997, 71, 3712-3714.	3.3	36
158	Nanometer level etching and deposition of Bi-Sr-Ca-Cu-O superconducting thin films. , 1996, , .		4
159	The influence of Bi-sticking coefficient in the growth of Bi(2212) thin film by ion beam sputtering. Thin Solid Films, 1996, 281-282, 510-512.	1.8	10
160	Comparison between Bi-superconductor thin films fabricated via co-deposition and layer-by-layer deposition by ion beam sputtering method. Thin Solid Films, 1996, 281-282, 517-520.	1.8	6
161	Molecular beam epitaxial growth of SrO and CaO with RHEED intensity oscillation. Journal of Low Temperature Physics, 1996, 105, 1337-1342.	1.4	13
162	Superconductivity and magnetic transitions of La2â˜’xCuOy system under 60kbar O2-HIP treatment. Physica C: Superconductivity and Its Applications, 1991, 185-189, 775-776.	1.2	0

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163	Partial silicides technology for tunable work function electrodes on high-k gate dielectrics - fermi level pinning controlled PtS/sub X/, for HfO/sub X/(N) pMOSFET. , 0, , .		15
164	Anomalous change of carrier transport property of ferroelectric Hf0.5Zr0.5O2 thin films in the first poling treatment. Japanese Journal of Applied Physics, 0, , .	1.5	0